DMT10H009LFG

100V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D MAX T_C = +25°C
100V	8.5mΩ @ V_{GS} = 10V	50A
	12.5mΩ @ V_{GS} = 4.5V	41A

Features and Benefits

- Low $R_{DS(ON)}$ – Ensures On State Losses are Minimized
- Excellent Q_{gd} x $R_{DS\ (ON)}$ Product (FOM)
- Advanced Technology for DC/DC Converters
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production Ensures More Reliable and Robust End Application
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description

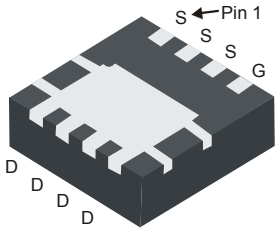
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

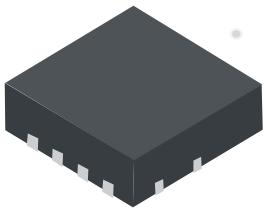
- Synchronous Rectifier
- Backlighting
- Power Management Functions
- DC-DC Converters

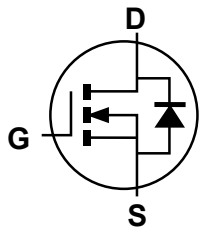
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.034 grams (Approximate)



Bottom View


Top View



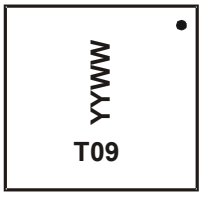
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT10H009LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMT10H009LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website athttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



T09 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)

Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 5) V_{GS} = 10V	T_A = +25°C	I_D	13	A
	T_A = +70°C		11	
	T_C = +25°C	I_D	50	A
	T_C = +70°C		40	
Maximum Continuous Body Diode Forward Current (Note 5)		I_S	25	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	200	A
Pulsed Body Diode Continuous Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	200	A
Avalanche Current (L = 1mH)		I_{AS}	17	A
Avalanche Energy (L = 1mH)		E_{AS}	144.5	mJ

Thermal Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	2	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	59	°C/W
Total Power Dissipation	T_C = +25°C	P_D	30	W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	3.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV_{DSS}	100	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 80V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.1	—	2.5	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	6.4	8.5	mΩ	V_{GS} = 10V, I_D = 20A
		—	8.2	12.5		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	2361	—	pF	V_{DS} = 50V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	611	—		
Reverse Transfer Capacitance	C_{rss}	—	16	—		
Gate Resistance	R_g	—	1.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	41	—	nC	V_{DD} = 50V, I_D = 13A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	7.3	—		
Gate-Drain Charge	Q_{gd}	—	9.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	7	—	ns	V_{DD} = 50V, V_{GS} = 10V, I_D = 13A, R_g = 6Ω
Turn-On Rise Time	t_R	—	12	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	42	—		
Turn-Off Fall Time	t_F	—	24	—		
Reverse Recovery Time	t_{RR}	—	45	—	ns	I_F = 13A, di/dt = 100A/µs
Reverse Recovery Charge	Q_{RR}	—	68	—	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.

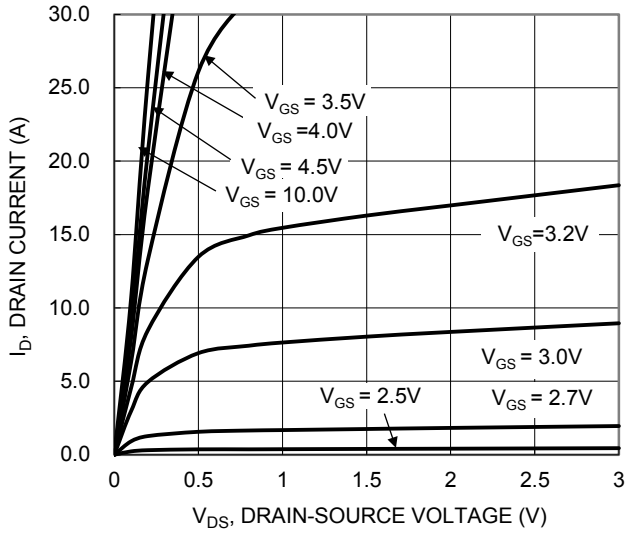


Figure 1. Typical Output Characteristic

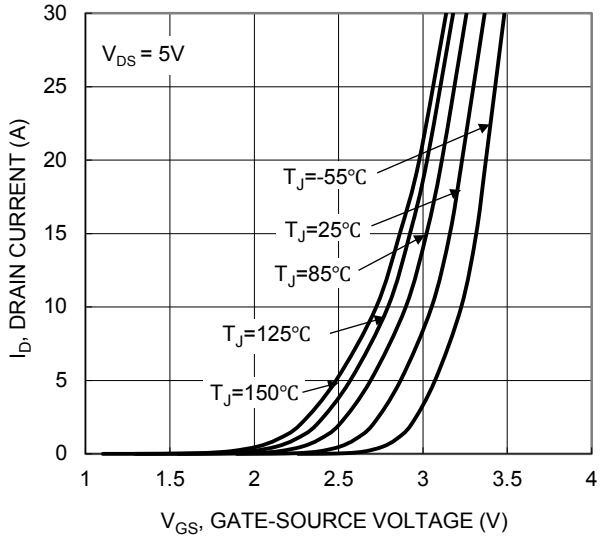


Figure 2. Typical Transfer Characteristic

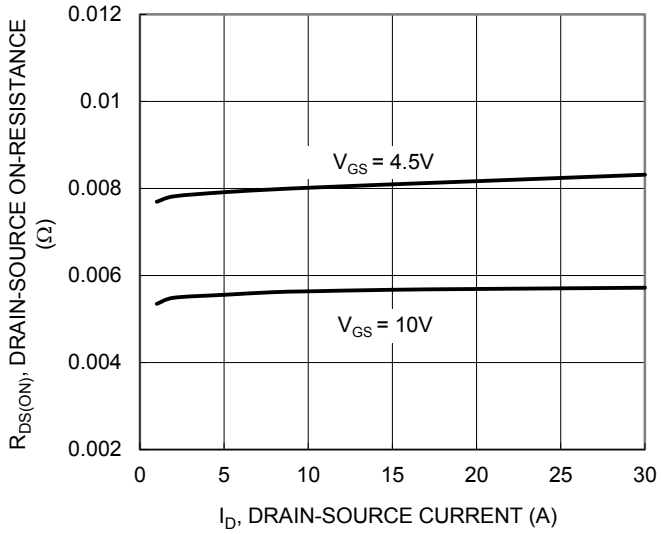


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

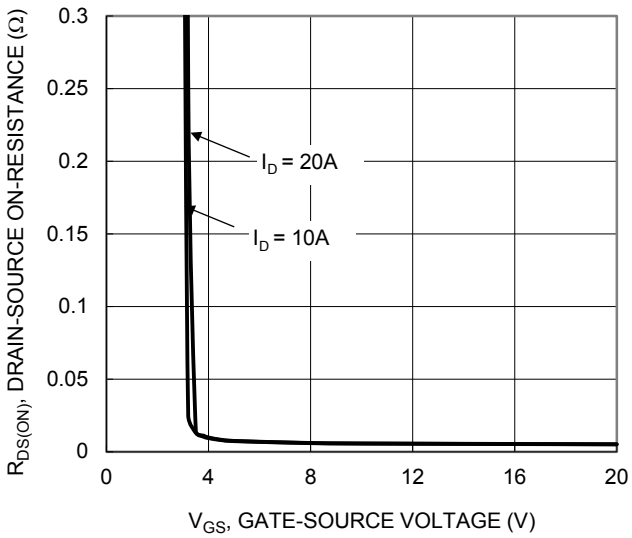


Figure 4. Typical Transfer Characteristic

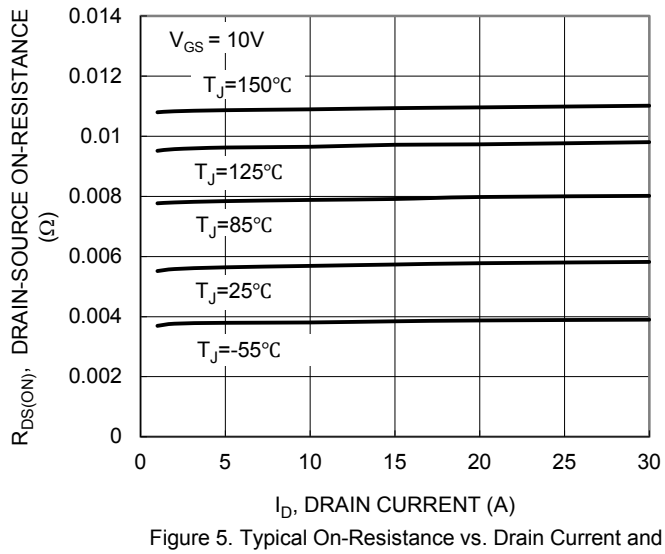


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

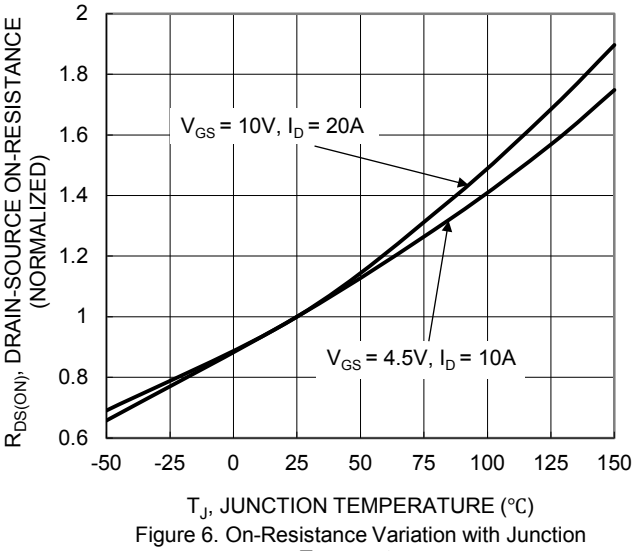


Figure 6. On-Resistance Variation with Junction Temperature

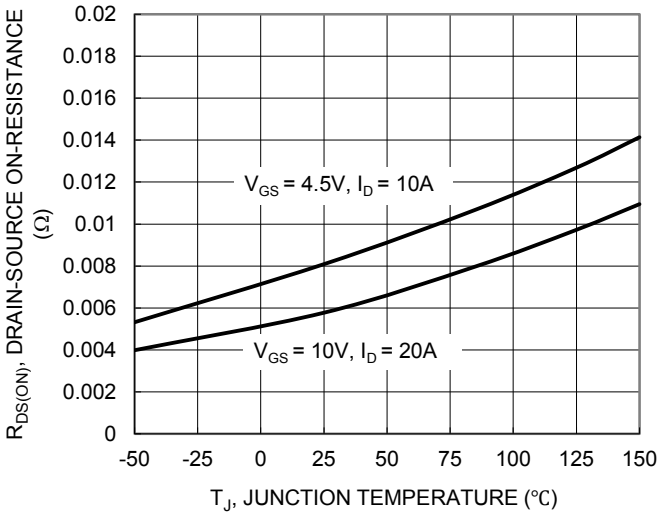


Figure 7. On-Resistance Variation with Junction Temperature

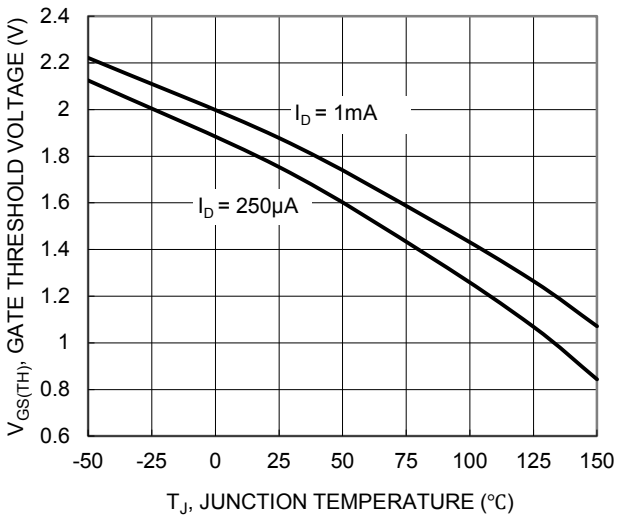


Figure 8. Gate Threshold Variation vs. Junction Temperature

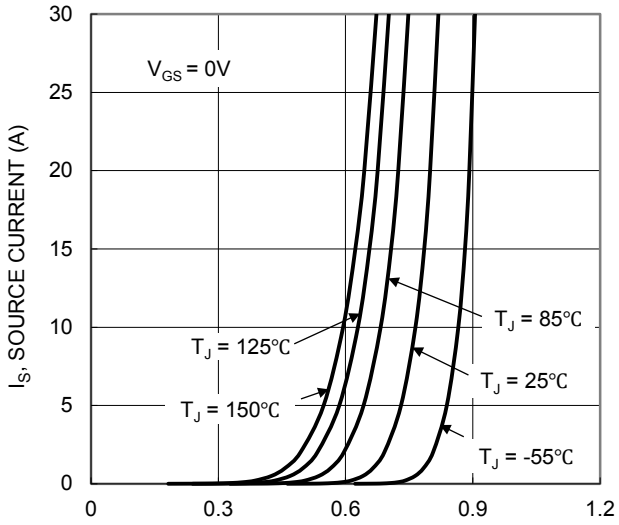


Figure 9. Diode Forward Voltage vs. Current

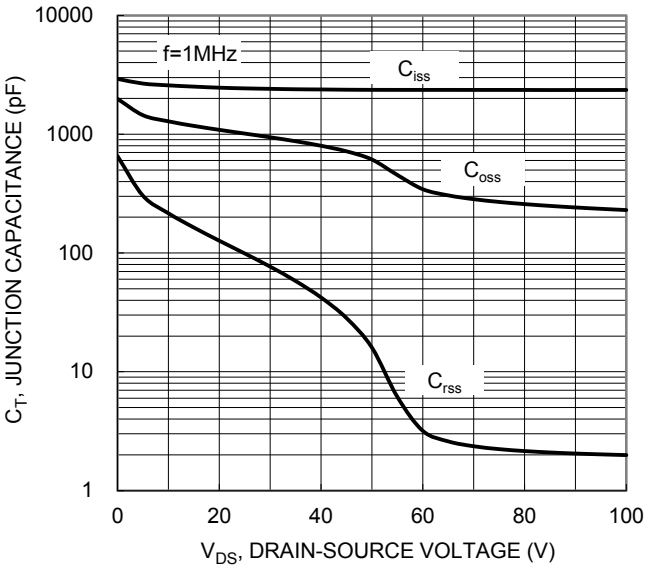


Figure 10. Typical Junction Capacitance

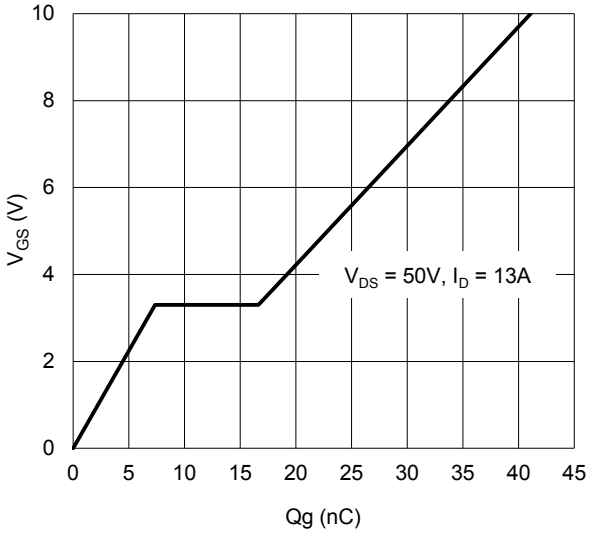


Figure 11. Gate Charge

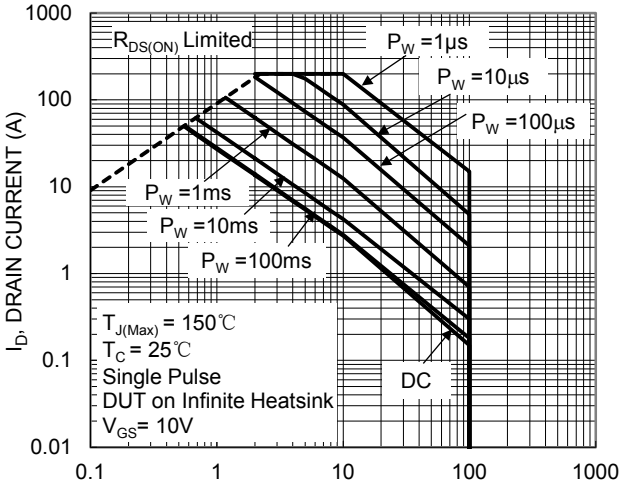


Figure 12. SOA, Safe Operation Area

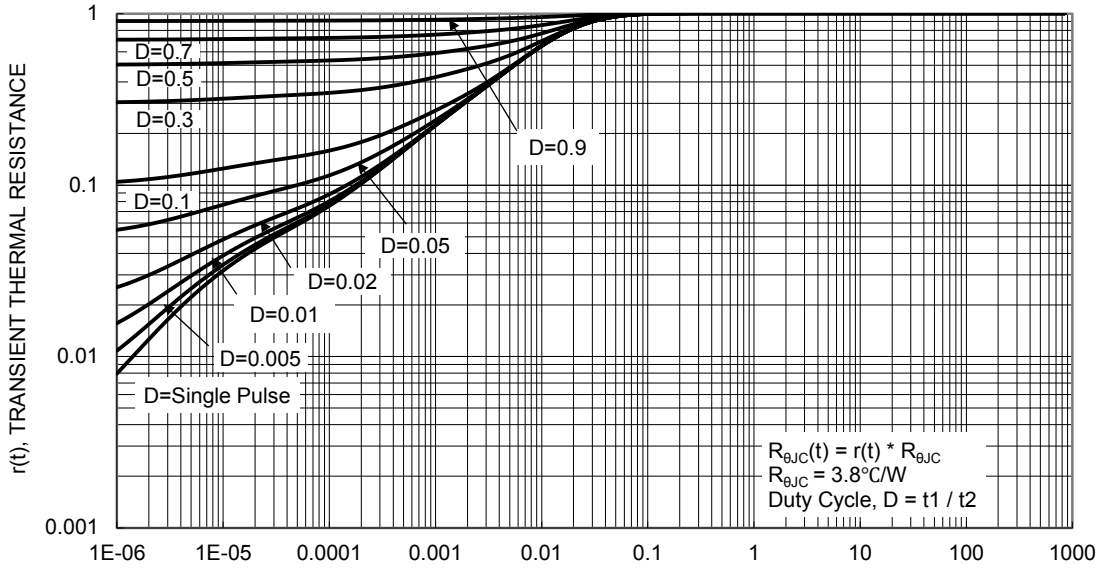
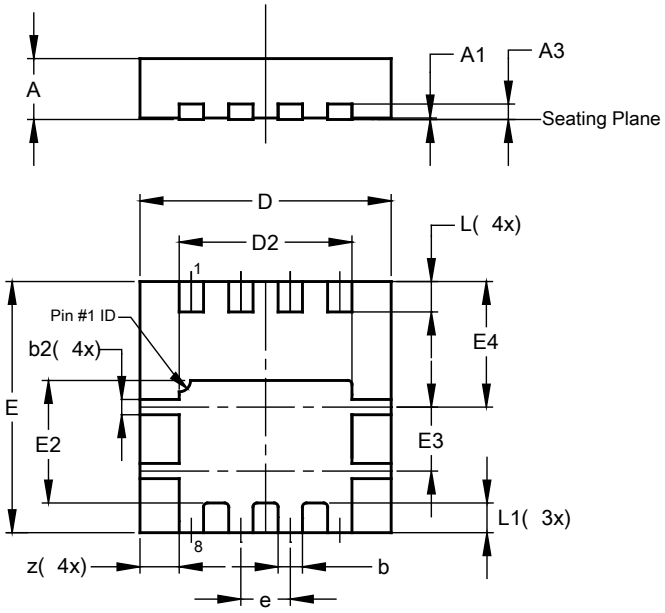


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

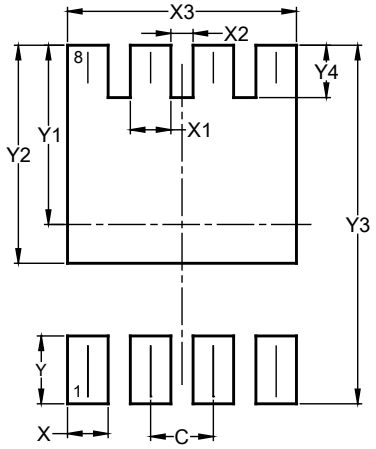


PowerDI3333-8			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	–	–	0.203
b	0.27	0.37	0.32
b2	0.15	0.25	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
E3	0.79	0.89	0.84
E4	1.60	1.70	1.65
e	–	–	0.65
L	0.35	0.45	0.40
L1	–	–	0.39
z	–	–	0.515
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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